

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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ATTY. DOCKET NO.
071971-0251SERIAL NO.
10/536,828APPLICANT
Makoto KITABATAKE, et al.FILING DATE
May 27, 2005GROUP
2814**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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EXAMINER
/Abul Kalam/DATE CONSIDERED
10/21/2009

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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /A.K./